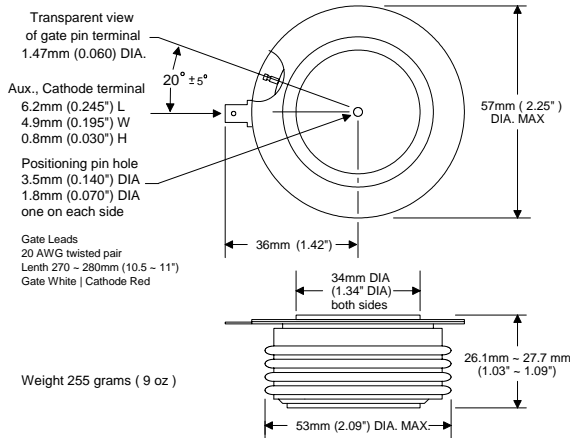


G package

JEDEC: TO-200AC



Part number scheme

G T 07 N 18 KNX

1 2 3 4 5 6

- 1) Package designation
- 2) Thyristor designation (i.e. SCR)
- 3) Series number
- 4) Designates standard recovery time
- 5) Voltage Multiplier (example: 30 x 100 = 1800)
- 6) Proprietary suffix

Features:

- ✓ All diffused silicone.
- ✓ Center amplifying gate.
- ✓ Standard recovery time for phase control applications.
- ✓ Disk press package (nick named, Hockey Puck)
- ✓ Metal and ceramic package construction.
- ✓ Double side cooling.

Voltage

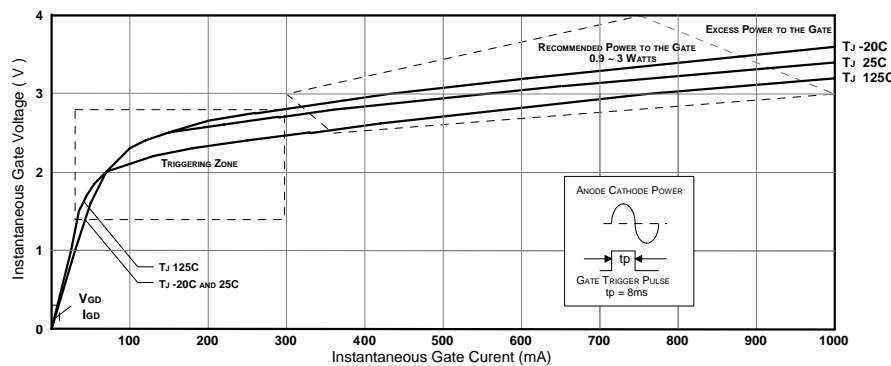
Parameter	Symbol	Rating	Units
Maximum Repetitive Off-State Voltage <small>Notes: 1, 3, 4, 5, 6, 7</small>	V _{DRM}	1600 ~ 2600	Volts
Maximum Repetitive Reverse Voltage <small>Notes: 1, 3, 4, 5, 6</small>	V _{RRM}	1600 ~ 2700	Volts
Maximum non repetitive Surge of Reverse Voltage <small>Notes: 2, 3, 4, 5, 6</small>	V _{RSM}	V _{RRM} + 100	Volts
Critical rate of rising off-state Voltage, Linear to 80% of V _{DRM} <small>Note: 2</small>	dv/dt	400	V/μs
<small>Note 1: T_J 25°C. Note 2: T_J 125°C. Note 3: Measured at the peak of the sine wave, Note 4: Below 0°C derate V_{DRM} and V_{RRM} 10%. Note 5: V_{DRM} and V_{RRM} have I_{DRM}, I_{RRM} of up to 35mA. Note 6: V_{DR} and V_{RR} have typical I_{DR}, I_{RR} of 2~7mA. Note 7: For DC applications derate V_{DRM} 45%.</small>			
Specifying voltage:	1800V, GT07N18 2200V, GT07N22 2600V, GT07N26		
	1600V, GT07N16 2000V, GT07N20 2400V, GT07N24 Above 2600V inquire for availability.		

Gate

Parameter	Symbol	Rating			Units
		Temp.	Typ.	Max.	
Gate Trigger Voltage <small>Note 3</small>	V _{GT}	-20°C 25°C 125°C	2.3 ~ 2.8 1.9 ~ 2.4 1.4 ~ 1.6	3	Volts
Maximum Gate Trigger Current <small>Notes 1,3</small>	I _{GT}		300		mA
Minimum Forward Current to Latch on-state <small>Notes 1,5</small>	I _L		800		mA
Maximum permissible Gate Voltage not to Trigger <small>Notes 1,3</small>	V _{GDM}		250		mV
Maximum permissible Gate Current not to Trigger <small>Notes 1,3</small>	I _{GDM}		10		mA
Maximum peak non repetitive Gate Voltage <small>Notes 2,3</small>	V _{GM}		8.4		Volts
Maximum Negative Gate Voltage <small>Notes 2,4</small>	-V _{GM}		5		Volts
Maximum non repetitive Gate Current <small>Notes 2,3</small>	I _{GM}		3.7		Amperes
Maximum Repetitive Gate Current <small>Notes 2,3</small>	I _{GRM}		1		Amperes
Average Gate Power (recommended) <small>Note 2,3</small>	P _{G(AVE)}		0.9 ~ 3		Watts
<small>Note 1: T_J 25°C. Note 2: T_J 125°C. Note 3: Rectangular pulse, t_p ≤ 8.3 ms. Note 4: Rectangular -V_{DC} pulse, t_p ≤ 8.3 ms. Note 5: Test conditions: I_{DC} R_L = 12Ω.</small>					

These graphs depict a typical device, each device has unique characteristics

Gate Characteristics



Maximum non repetitive GATE POWER (P_{GM})

